
Oral presentation | 14. Semiconductors B (Exploratory Materials, Physical Properties, Devices) | 14.3 Electron devices and Process technology

[19p-D7-1~17]14.3 Electron devices and Process technology

Thu. Sep 19, 2013 1:00 PM - 5:45 PM D7 (MK 3F-302)

△ : Young Scientist Oral Presentation Award Applied

▲ : English Presentation

▼ : Both Award Applied and English Presentation

1:00 PM - 1:30 PM

[19p-D7-1][JSAP Paper Award Speech](30 min.)Inverted-Type InGaAs Metal– Oxide– Semiconductor High-Electron-Mobility Transistor on Si Substrate with Maximum Drain Current Exceeding 2A/mm

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